

ABSTRACT OF THE DISCLOSURE

Claimed and disclosed is a semiconductor device including a transistor having a gate insulating film structure containing nitrogen or fluorine in a compound, such as metal silicate, containing metal, silicon and oxygen, a gate insulating film structure having a laminated structure of an amorphous metal oxide film and metal silicate film, or a gate insulating film structure having a first gate insulating film including an oxide film of a first metal element and a second gate insulating film including a metal silicate film of a second metal element.